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PATENT
29936/37830
2/25/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Dae Gyu Park et al.

Serial No.: 10/036,156

Filed: December 26, 2001

For: Method of Forming a Metal Gate in a Semiconductor Device Using Atomic Layer Deposition Process (as amended)

Group Art Unit: 2813

Examiner: Jack S.J. Chen

I hereby certify that this paper is being deposited with the United States Postal Service as first class mail, postage prepaid, in an envelope addressed to: Commissioner for Patents, Washington, DC 20231 on February 6, 2003

Michael R. Hill
Reg. No. 85,902
Attorney for Applicants

AMENDMENT

Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated November 06, 2002, the following amendments and remarks are respectfully submitted in connection with the above-identified application:

In the Specification:

Please replace the title with the following new title:

--METHOD OF FORMING A METAL GATE IN A SEMICONDUCTOR DEVICE USING ATOMIC LAYER DEPOSITION PROCESS--

RECEIVED
FEB 11 2003
TECHNOLOGY CENTER 2800